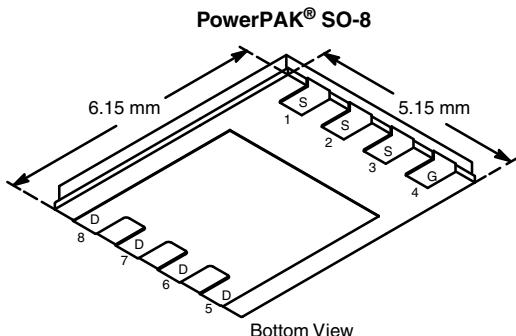


N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)	Q_g (Typ.)
150	0.0180 at $V_{GS} = 10$ V	53.7	31.5 nC
	0.0200 at $V_{GS} = 7.5$ V	51	



Ordering Information:
SiR872DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

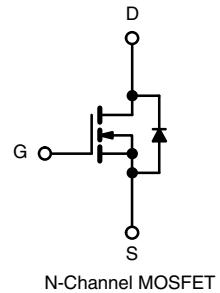
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Fixed Telecom
- DC/DC Converter
- Primary and Secondary Side Switch



ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V_{DS}	150	V		
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150$ °C)	I_D	53.7 43 12.8 ^{b, c} 10.2 ^{b, c}	A		
		$T_C = 25$ °C $T_C = 70$ °C $T_A = 25$ °C $T_A = 70$ °C			
Pulsed Drain Current ($t = 300$ μ s)	I_{DM}	100			
Continuous Source-Drain Diode Current	I_S	60 ^a 5.6 ^{b, c}			
Single Pulse Avalanche Current	I_{AS}	30	W		
Single Pulse Avalanche Energy	E_{AS}	45			mJ
Maximum Power Dissipation	P_D	104 66.6 6.25 ^{b, c} 4 ^{b, c}			
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150			°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260			

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R_{thJA}	15	20	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	0.9	1.2	

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 54 °C/W.

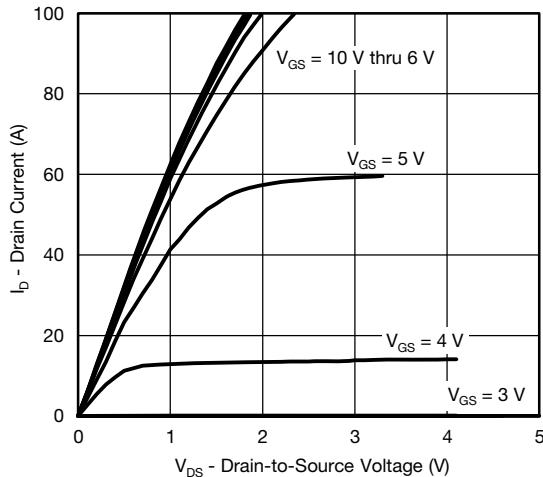
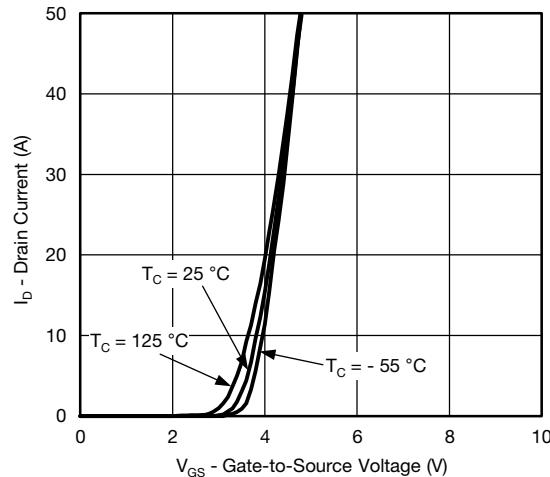
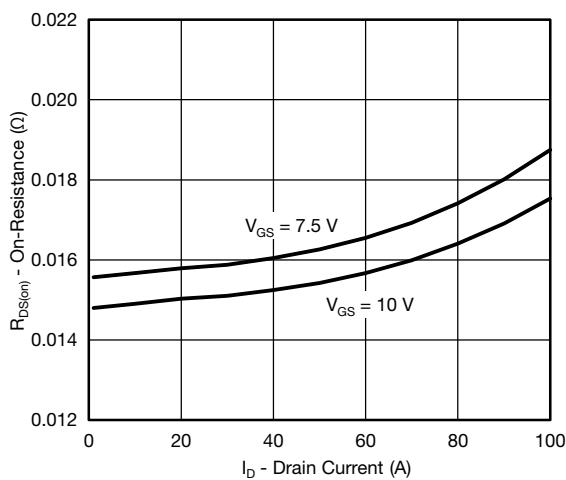
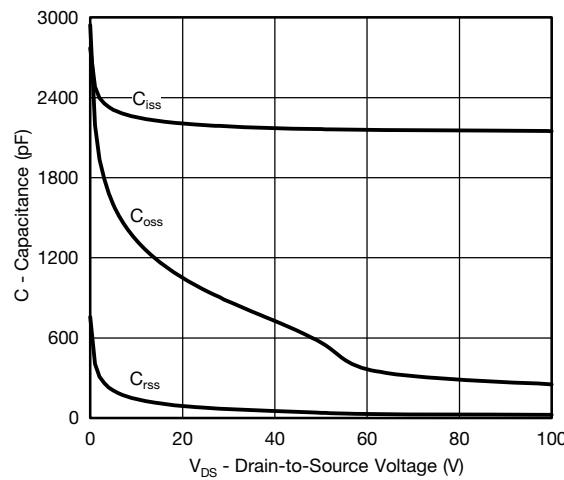
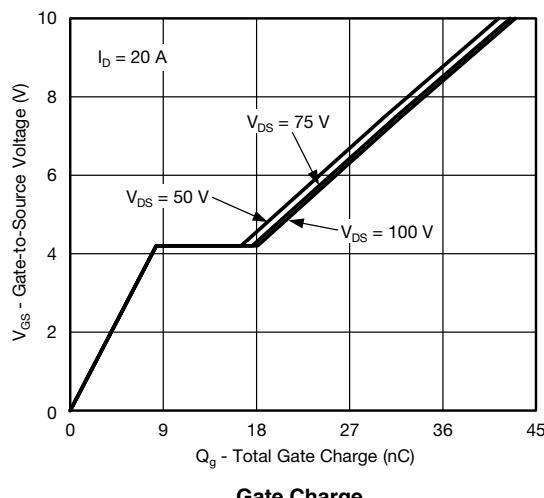
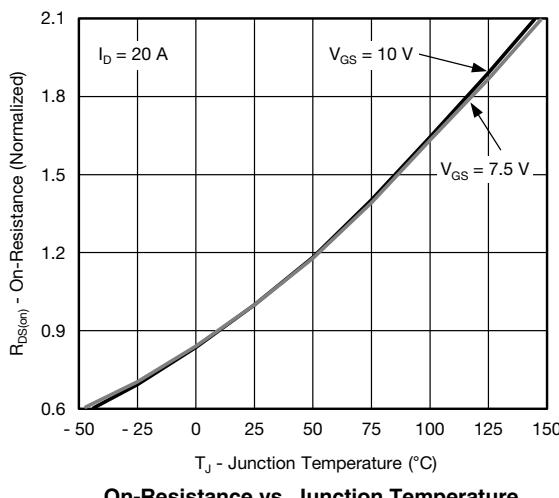
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	150			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		110		mV°C
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			5.6		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$		1.5		3.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 150 \text{ V}$, $V_{GS} = 0 \text{ V}$		1		μA
		$V_{DS} = 150 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$		10		
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$, $V_{GS} = 10 \text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 20 \text{ A}$		0.0148	0.0180	Ω
		$V_{GS} = 7.5 \text{ V}$, $I_D = 15 \text{ A}$		0.0153	0.0200	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10 \text{ V}$, $I_D = 20 \text{ A}$		42		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 75 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		2130		pF
Output Capacitance	C_{oss}			285		
Reverse Transfer Capacitance	C_{rss}			27		
Total Gate Charge	Q_g	$V_{DS} = 75 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 20 \text{ A}$		42.5	64	nC
				31.5	50	
Gate-Source Charge	Q_{gs}	$V_{DS} = 75 \text{ V}$, $V_{GS} = 7.5 \text{ V}$, $I_D = 20 \text{ A}$		8.5		
Gate-Drain Charge	Q_{gd}			9.5		
Output Charge	Q_{oss}	$V_{DS} = 75 \text{ V}$, $V_{GS} = 0 \text{ V}$		62.5	94	
Gate Resistance	R_g	$f = 1 \text{ MHz}$	0.3	1	2	Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 75 \text{ V}$, $R_L = 3.75 \Omega$ $I_D \geq 20 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 1 \Omega$		15	30	ns
Rise Time	t_r			9	18	
Turn-Off Delay Time	$t_{d(\text{off})}$			28	56	
Fall Time	t_f			8	16	
Turn-On Delay Time	$t_{d(\text{on})}$			19	38	
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(\text{off})}$			25	50	
Fall Time	t_f			8	16	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			60	A
Pulse Diode Forward Current ^a	I_{SM}				100	
Body Diode Voltage	V_{SD}	$I_S = 5 \text{ A}$		0.78	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10 \text{ A}$, $dl/dt = 100 \text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$		95	190	ns
Body Diode Reverse Recovery Charge	Q_{rr}			280	560	
Reverse Recovery Fall Time	t_a			54		ns
Reverse Recovery Rise Time	t_b			41		

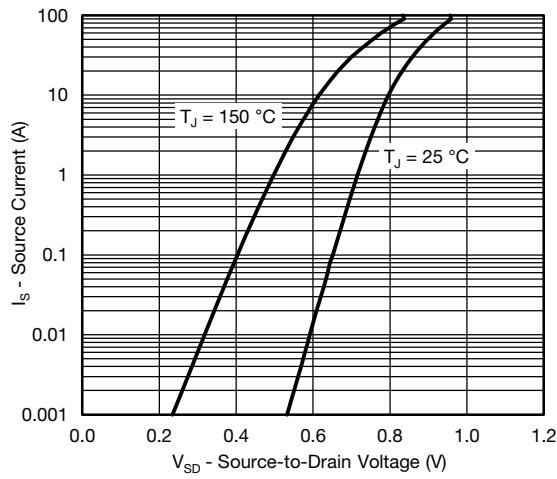
Notes:

a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$.
b. Guaranteed by design, not subject to production testing.

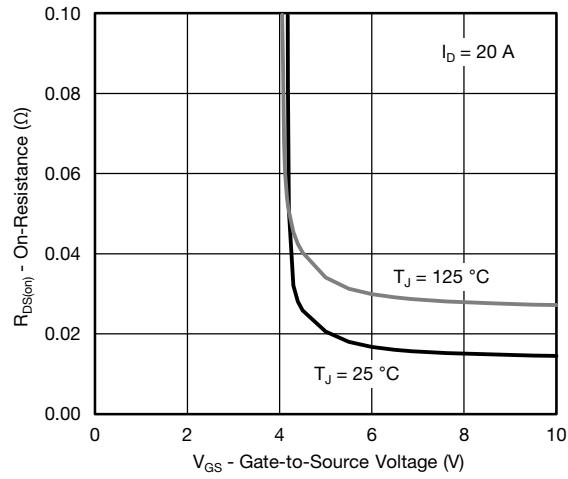
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

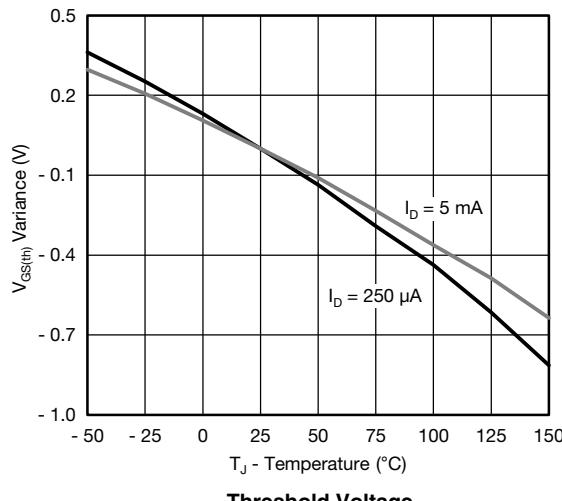
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



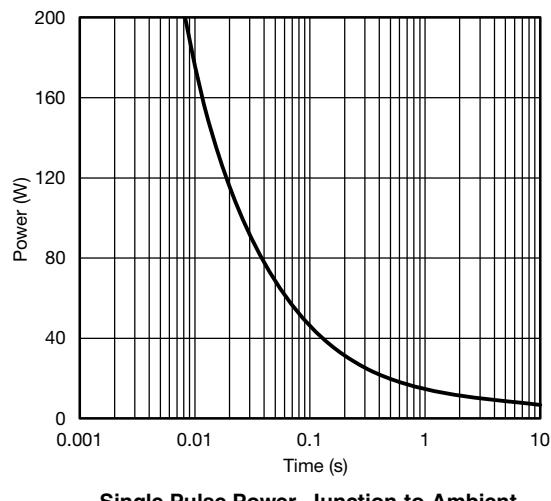
Source-Drain Diode Forward Voltage



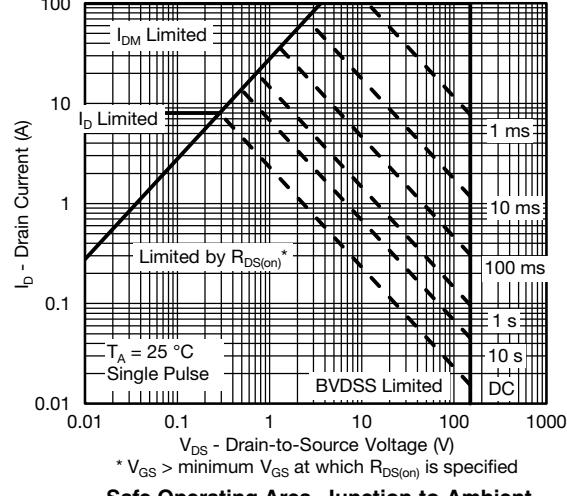
On-Resistance vs. Gate-to-Source Voltage



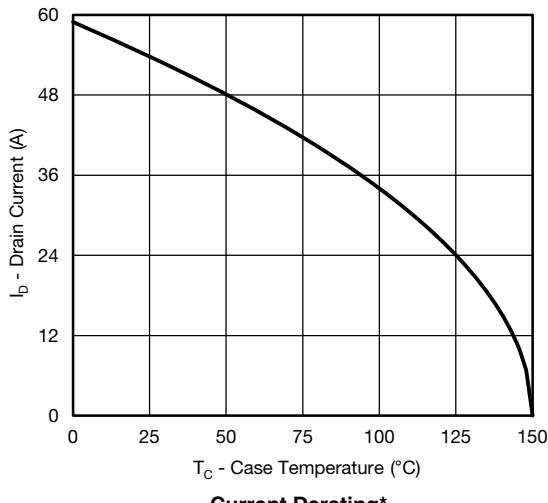
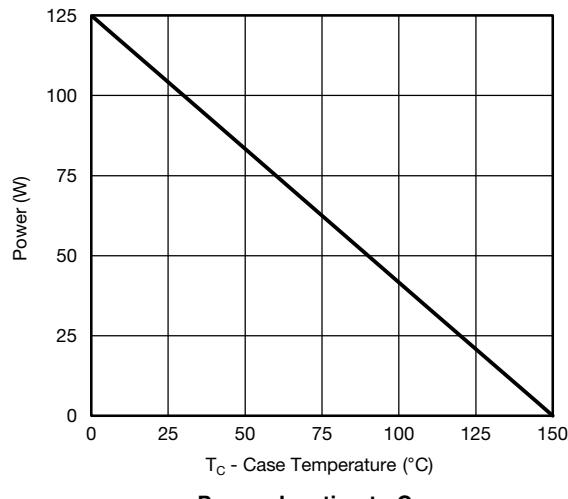
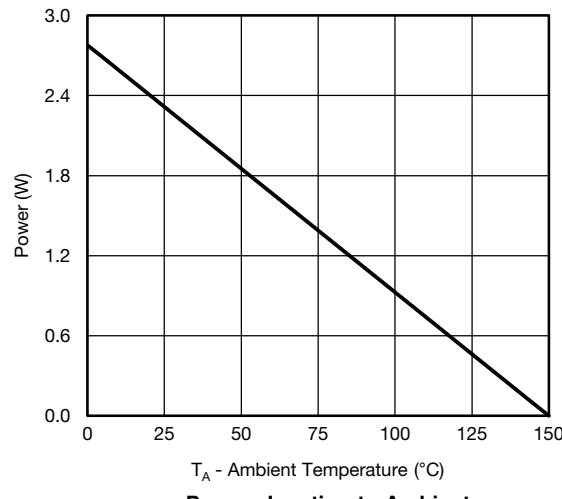
Threshold Voltage



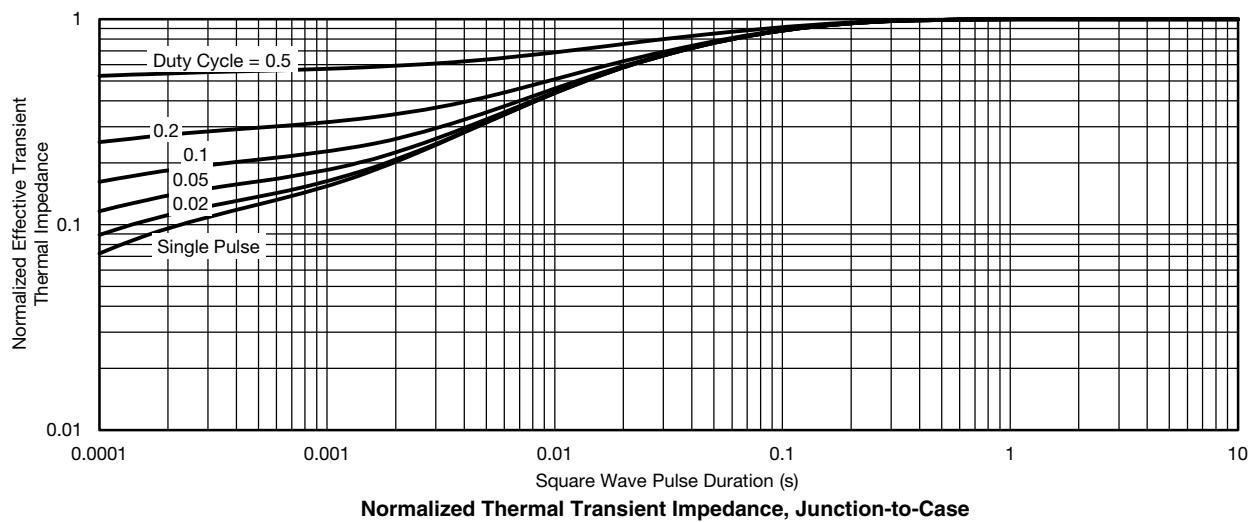
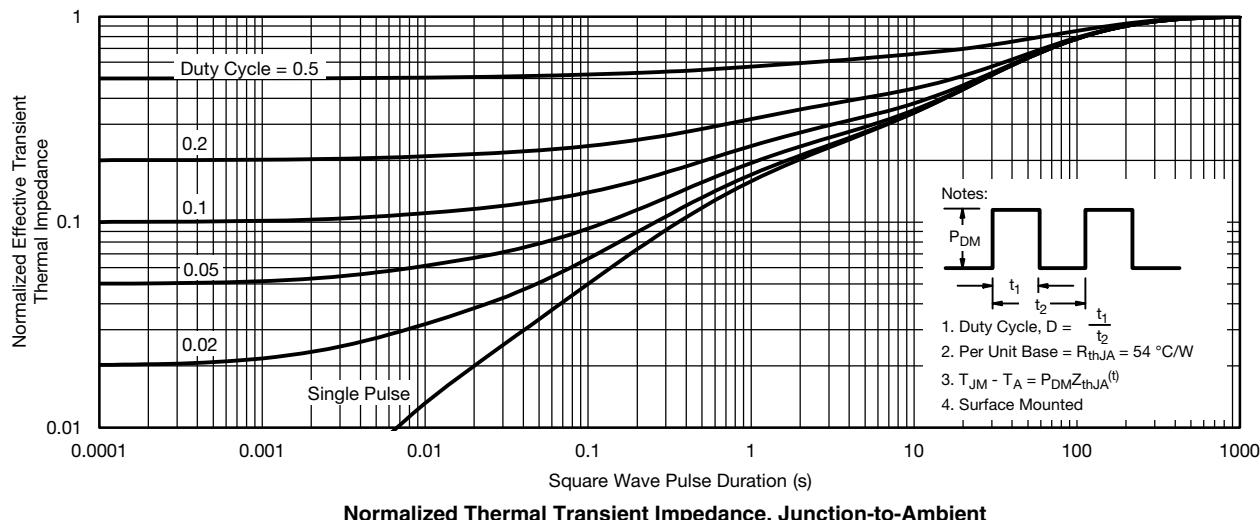
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

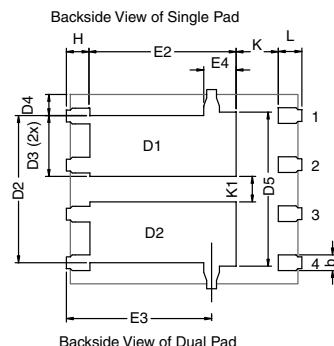
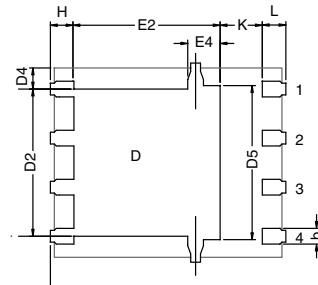
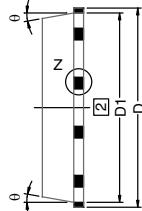
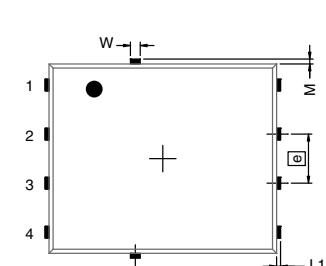
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating*

Power, Junction-to-Case

Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(\text{max})} = 150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63809.

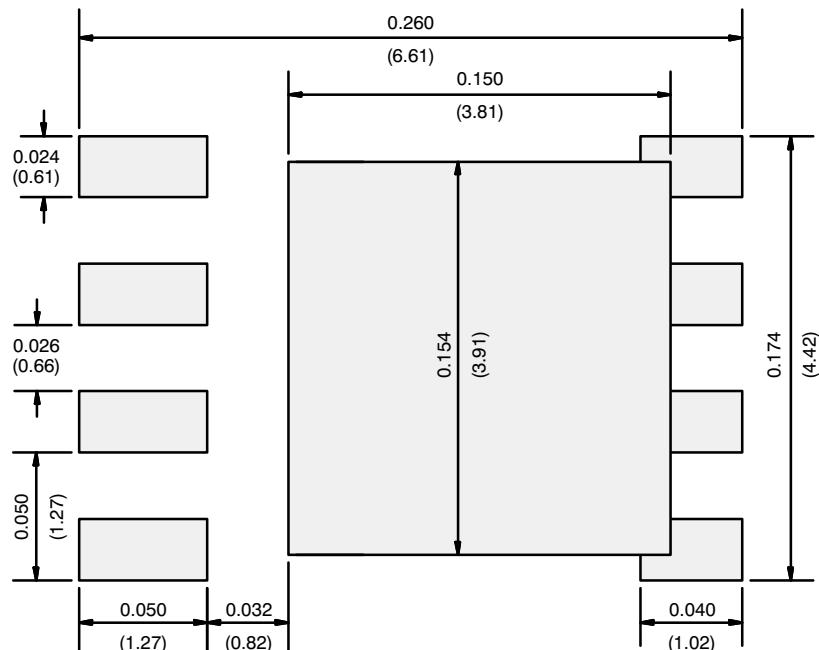
PowerPAK® SO-8, (Single/Dual)


Notes

1. Inch will govern.
2. Dimensions exclusive of mold gate burrs.
3. Dimensions exclusive of mold flash and cutting burrs.

DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
A	0.97	1.04	1.12	0.038	0.041	0.044	
A1		-	0.05	0	-	0.002	
b	0.33	0.41	0.51	0.013	0.016	0.020	
c	0.23	0.28	0.33	0.009	0.011	0.013	
D	5.05	5.15	5.26	0.199	0.203	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.56	3.76	3.91	0.140	0.148	0.154	
D3	1.32	1.50	1.68	0.052	0.059	0.066	
D4	0.57 typ.			0.0225 typ.			
D5	3.98 typ.			0.157 typ.			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	5.79	5.89	5.99	0.228	0.232	0.236	
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144	
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151	
E3	3.68	3.78	3.91	0.145	0.149	0.154	
E4 (for AL product)	0.58 typ.			0.023 typ.			
E4 (for other product)	0.75 typ.			0.030 typ.			
e	1.27 BSC			0.050 BSC			
K (for AL product)	1.45 typ.			0.057 typ.			
K (for other product)	1.27 typ.			0.050 typ.			
K1	0.56	-	-	0.022	-	-	
H	0.51	0.61	0.71	0.020	0.024	0.028	
L	0.51	0.61	0.71	0.020	0.024	0.028	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
M	0.125 typ.			0.005 typ.			

ECN: C13-0702-Rev. K, 20-May-13
DWG: 5881

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single

Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)

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